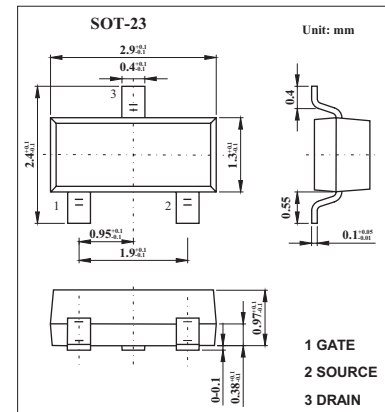
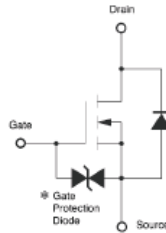


Silicon N-Channel MOSFET

2SK2731

Features

- Low on-resistance.
- Fast switching speed.
- Easily designed drive circuits.
- Easy to parallel.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	0.2	A
	I _{DP} *	0.8	A
Power dissipation	P _D	0.2	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, Duty Cycle ≤ 1%

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain source breakdown voltage	V _{DSS}	I _D =1mA, V _{GS} =0V	30			V
Drain cut-off current	I _{DSS}	V _{DS} =30V, V _{GS} =0			10	μA
Gate leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±10	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =10V, I _D =1mA	1.0		2.5	V
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =0.1A	100			ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =10V, I _D =0.1A		1.5	2.8	Ω
		V _{GS} =4V, I _D =0.1A		2.8	4.5	Ω
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHz		25		pF
Output capacitance	C _{oss}			15		pF
Reverse transfer capacitance	C _{rss}			10		pF
Turn-on delay time	t _{on}				15	
Rise time	t _r	I _D =0.1A, V _{GS(on)} =10V, R _G =10Ω, R _L =150Ω, V _{DD} =15V		20		ns
Turn-off delay time	t _{off}			90		ns
Fall time	t _f			100		ns

Marking

Marking	KL
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